PSRAM 4-Mbit (256K x 16) Pseudo Static RAM

Features

• Advanced low-power architecture

•High speed: 55 ns, 60 ns and 70 ns

•Wide voltage range: 2.7V to 3.6V

•Typical active current: 1 mA @ f = 1 MHz

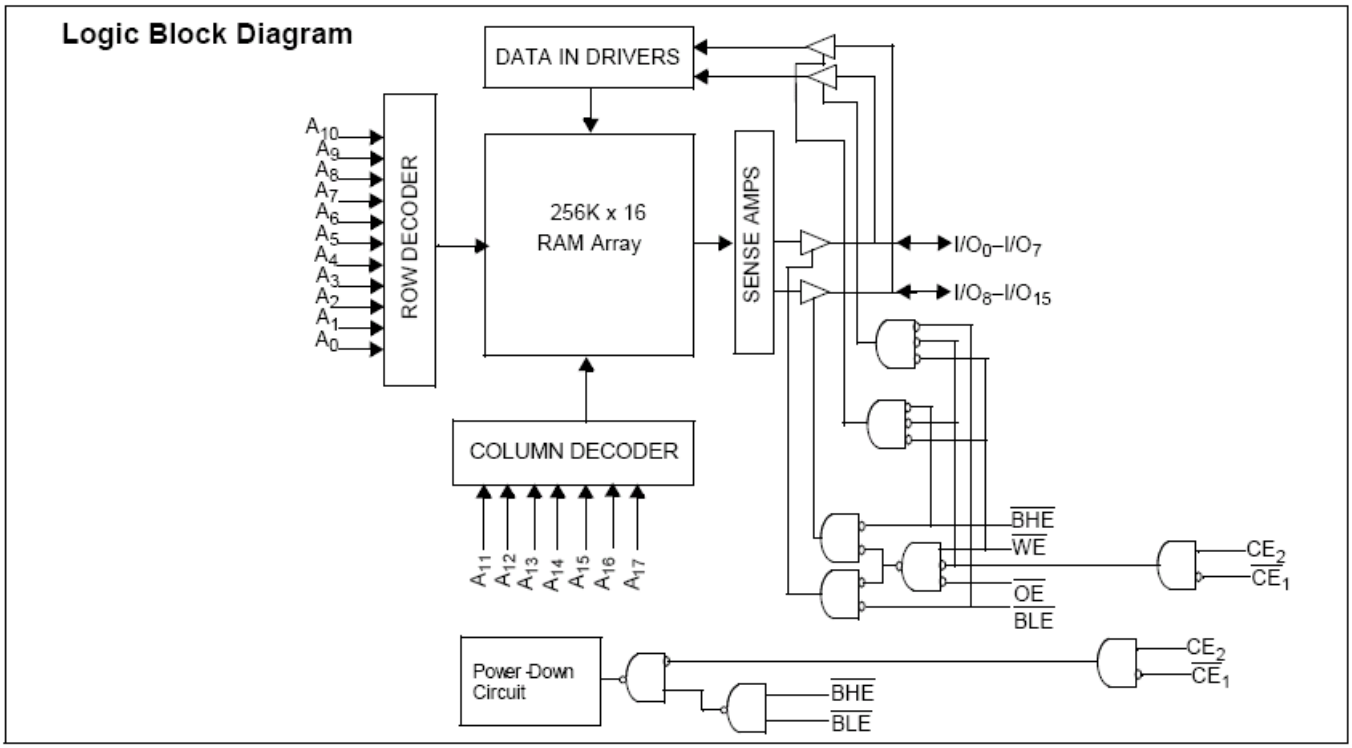
•Low standby power

•Automatic power-down when deselected

Functional Description

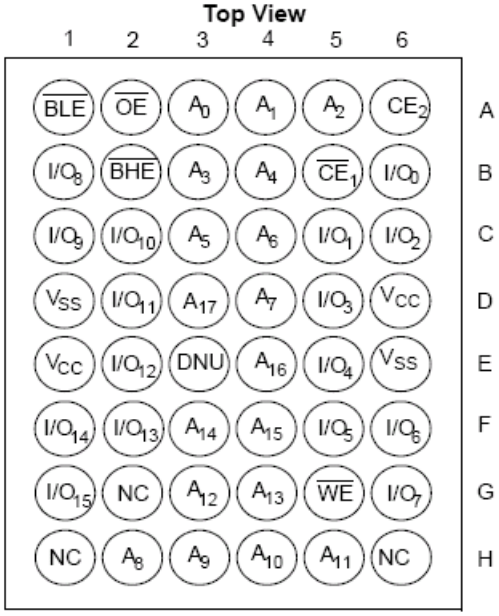
The M24L416256DA is a high-performance CMOS pseudo static RAM (PSRAM) organized as 256K words by 16 bits that supports an asynchronous memory interface. This device features advanced circuit design to provide ultra-low active current. This is ideal for portable applications such as cellular telephones. The device can be put into standby mode reducing power consumption dramatically when deselected ($\overline{CE}$1 HIGH, CE2 LOW or both $\overline{BHE}$ and $\overline{BLE}$ are HIGH). The input/output pins (I/O_0 through I/O_{15}) are placed in a high-impedance state when: deselected ($\overline{CE}$1 HIGH, CE2 LOW, $\overline{OE}$ is HIGH), or during a write operation (Chip Enabled and Write Enable $\overline{WE}$ LOW).

Reading from the device is accomplished by asserting the Chip Enables ($\overline{CE}$1 LOW and CE2 HIGH) and Output Enable($\overline{OE}$) LOW while forcing the Write Enable ($\overline{WE}$) HIGH. If Byte Low Enable ($\overline{BLE}$) is LOW, then data from the memory location specified by the address pins A0 through A17 will appear on I/O_0 to I/O_7. If Byte High Enable ($\overline{BHE}$) is LOW, then data from memory will appear on I/O_8 to I/O_{15}. See the Truth Table for a complete description of read and write modes.

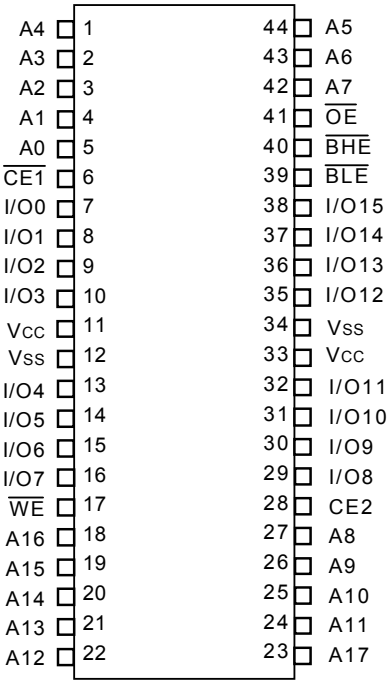


Pin Configuration[3, 4, 5]

48-ball VFBGA
Top View



44-pin TSOPII
Top View



Product Portfolio

Product	V_{CC} Range(V)			Speed (ns)	Power Dissipation					
					Operating, ICC (mA)				Standby, ISB2 (μA)	
					f = 1 MHz		f = f_{MAX}			
	Min.	Typ.	Max.		Typ.[2]	Max.	Typ.[2]	Max.	Typ.[2]	Max.
M24L416256DA	2.7	3.0	3.6	55	1	5	14	22	17	40
				60						
				70			8	15		

Notes:
2.Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V_{CC} = $V_{CC\ (typ)}$ and T_A = 25°C.
3.Ball H1, G2, H6 are the address expansion pins for the 8-Mb, 16-Mb, and 32-Mb densities, respectively.
4.NC “no connect”—not connected internally to the die.
5.DNU (Do Not Use) pins have to be left floating or tied to V_{SS} to ensure proper application.

Maximum Ratings

(Above which the useful life may be impaired. For user guide-lines, not tested.)
Storage Temperature .....–65°C to +150°C
Ambient Temperature with
Power Applied .....–55°C to +125°C
Supply Voltage to Ground Potential .....−0.4V to 4.6V
DC Voltage Applied to Outputs
in High-Z State[6, 7, 8] .....−0.4V to 3.7V
DC Input Voltage[6, 7, 8] .....−0.4V to 3.7V
Output Current into Outputs (LOW) .....20 mA
Static Discharge Voltage ..... > 2001V
(per MIL-STD-883, Method 3015)
Latch-up Current .....> 200 mA

Operating Range

Range	Ambient Temperature (T_A)	V_{CC}
Extended	−25°C to +85°C	2.7V to 3.6V
Industrial	−40°C to +85°C	2.7V to 3.6V

DC Electrical Characteristics (Over the Operating Range)

Parameter	Description	Test Conditions		-55, 60, 70			Unit
				Min.	Typ.[2]	Max.	
V_{CC}	Supply Voltage			2.7	3.0	3.6	V
V_{OH}	Output HIGH Voltage	I_{OH} = −0.1 mA		V_{CC} – 0.4			V
V_{OL}	Output LOW Voltage	I_{OL} = 0.1 mA				0.4	V
V_{IH}	Input HIGH Voltage			0.8 * V_{CC}		V_{CC} + 0.4	V
V_{IL}	Input LOW Voltage	F = 0		-0.4		0.62	V
I_{IX}	Input Leakage Current	GND ≤ V_{IN} ≤ Vcc		-1		+1	µA
I_{OZ}	Output Leakage Current	GND ≤ V_{OUT} ≤ Vcc, Output Disabled		-1		+1	µA
I_{CC}	V_{CC} Operating Supply Current	f = f_{MAX} = 1/t_{RC}	V_{CC} = 3.6V, I_{OUT} = 0 mA, CMOS level		14 for –55 14 for –60 08 for –70	22 for –55 22 for –60 15 for –70	mA
		f = 1 MHz			1 for all speeds	5 for all speeds	
I_{SB1}	Automatic $\overline{CE1}$ Power-down Current —CMOS Inputs	$\overline{CE1}$ ≥ V_{CC} − 0.2V, CE2 ≤ 0.2V, V_{IN} ≥ V_{CC} − 0.2V, V_{IN} ≤ 0.2V, f = f_{MAX}(Address and Data Only),f = 0 ($\overline{OE}$, $\overline{WE}$, $\overline{BHE}$ and $\overline{BLE}$)			150	250	µA
I_{SB2}	Automatic $\overline{CE1}$ Power-down Current —CMOS Inputs	$\overline{CE1}$ ≥ V_{CC} − 0.2V, CE2 ≤ 0.2V, V_{IN} ≥ V_{CC} − 0.2V or V_{IN} ≤ 0.2V, f = 0, V_{CC} = 3.6V			17	40	µA

Capacitance[9]

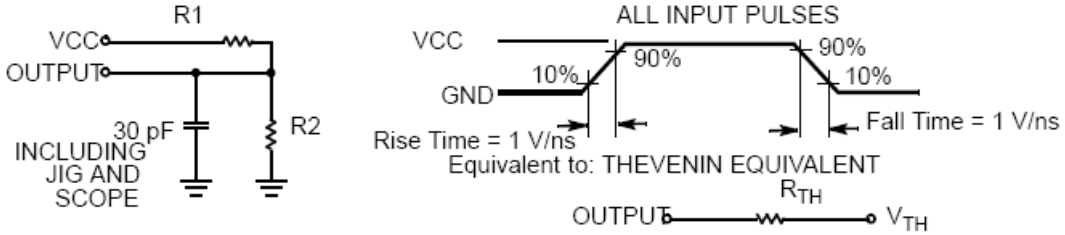
Parameter	Description	Test Conditions	Max.	Unit
C_{IN}	Input Capacitance	T_A = 25°C, f = 1 MHz V_{CC} = $V_{CC(typ)}$	8	pF
C_{OUT}	Output Capacitance		8	pF

Thermal Resistance[9]

Parameter	Description	Test Conditions	VFBGA	Unit
θ_{JA}	Thermal Resistance (Junction to Ambient)	Test conditions follow standard test methods and procedures for measuring thermal impedance, per EIA/JESD51.	55	°C/W
θ_{JC}	Thermal Resistance (Junction to Case)		17	°C/W

Notes:
6.$V_{IH(MAX)}$ = V_{CC} + 0.5V for pulse durations less than 20 ns.
7.$V_{IL(MIN)}$ = –0.5V for pulse durations less than 20 ns.
8.Overshoot and undershoot specifications are characterized and are not 100% tested.
9.Tested initially and after design or process changes that may affect these parameters.

AC Test Loads and Waveforms



Parameters	3.0V V_{CC}	Unit
R1	22000	Ω
R2	22000	Ω
R_{TH}	11000	Ω
V_{TH}	1.50	V

Switching Characteristics (Over the Operating Range)[10]

Prameter	Description	–55		–60		–70		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	
Read Cycle								
t_{RC}	Read Cycle Time	55[14]		60		70		ns
t_{AA}	Address to Data Valid		55		60		70	ns
t_{OHA}	Data Hold from Address Change	5		8		10		ns
t_{ACE}	$\overline{CE}$1 LOW and CE2 HIGH to Data Valid		55		60		70	ns
t_{DOE}	$\overline{OE}$ LOW to Data Valid		25		25		35	ns
t_{LZOE}	$\overline{OE}$ LOW to Low Z[11, 12]	5		5		5		ns
t_{HZOE}	$\overline{OE}$ HIGH to High Z[11, 12]		25		25		25	ns
t_{LZCE}	$\overline{CE}$1 LOW and CE2 HIGH to Low Z[11, 12]	5		5		5		ns
t_{HZCE}	$\overline{CE}$1 HIGH and CE2 LOW to High Z[11, 12]		25		25		25	ns
t_{DBE}	$\overline{BLE}$ / $\overline{BHE}$ LOW to Data Valid		55		60		70	ns
t_{LZBE}	$\overline{BLE}$ / $\overline{BHE}$ LOW to Low Z[11, 12]	5		5		5		ns
t_{HZBE}	$\overline{BLE}$ / $\overline{BHE}$ HIGH to High-Z[11, 12]		10		10		25	ns
t_{SK} [14]	Address Skew		0		5		10	ns
Write Cycle[13]								
t_{WC}	Write Cycle Time	55		60		70		ns
t_{SCE}	$\overline{CE}$1 LOW and CE2 HIGH to Write End	45		45		60		ns
t_{AW}	Address Set-up to Write End	45		45		55		ns
t_{HA}	Address Hold from Write End	0		0		0		ns
t_{SA}	Address Set-up to Write Start	0		0		0		ns

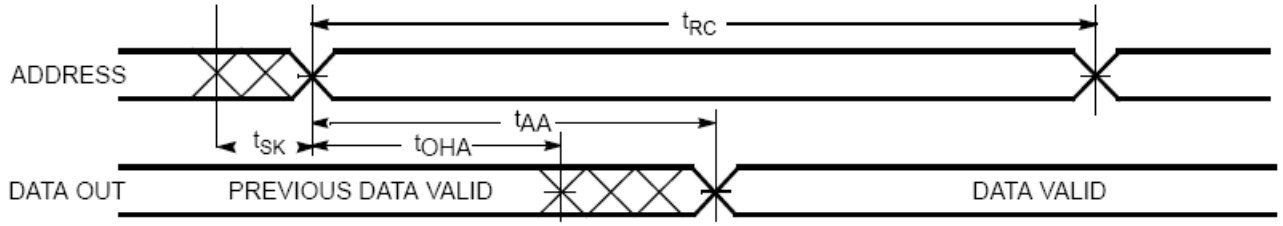
Notes:
10. Test conditions assume signal transition time of 1 V/ns or higher, timing reference levels of $V_{CC(typ)}/2$, input pulse levels of 0V to $V_{CC(typ)}$, and output loading of the specified I_{OL}/I_{OH} and 30-pF load capacitance.
11. t_{HZOE}, t_{HZCE}, t_{HZBE} and t_{HZWE} transitions are measured when the outputs enter a high-impedance state.
12. High-Z and Low-Z parameters are characterized and are not 100% tested.
13. The internal write time of the memory is defined by the overlap of $\overline{WE}$, $\overline{CE}$1 = V_{IL}, CE2 = V_{IH}, BHE and/or BLE =V_{IL}. All signals must be ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input set-up and hold timing should be referenced to the edge of the signal that terminates write.
14. To achieve 55-ns performance, the read access should be $\overline{CE}$ controlled. In this case t_{ACE} is the critical parameter and t_{SK} is satisfied when the addresses are stable prior to chip enable going active. For the 70-ns cycle, the addresses must be stable within 10 ns after the start of the read cycle.

Switching Characteristics (Over the Operating Range)[10] (continued)

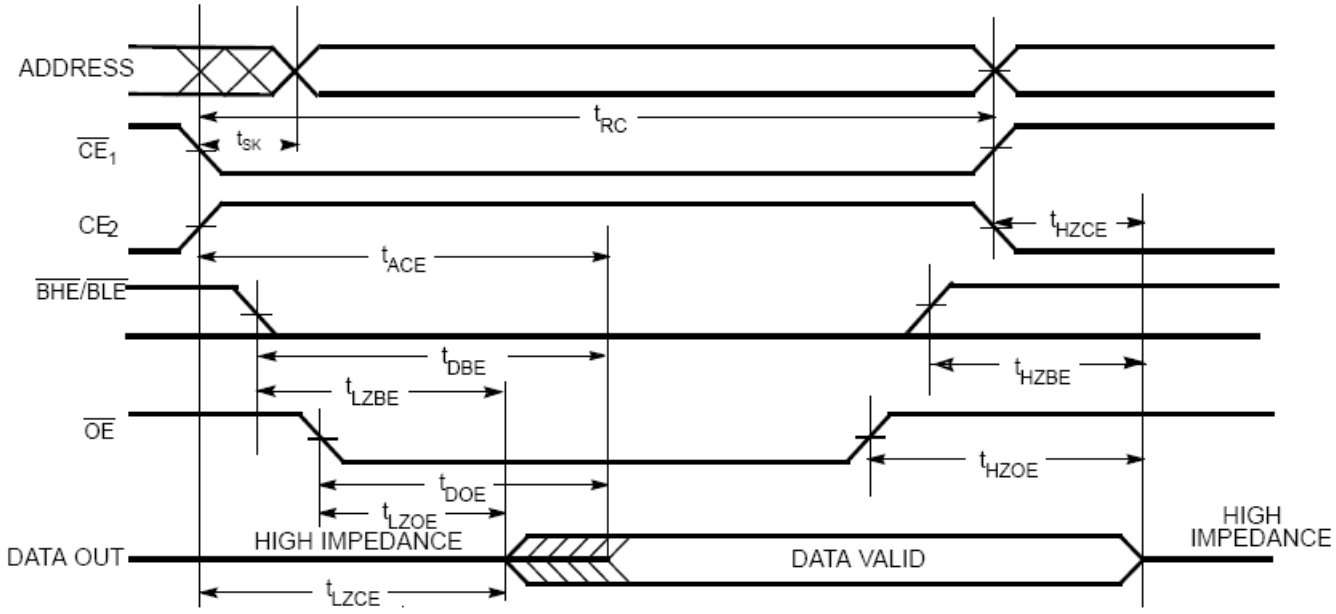
Prameter	Description	–55		–60		–70		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	
t_{PWE}	$\overline{WE}$ Pulse Width	40		40		45		ns
t_{BW}	$\overline{BLE}$ / $\overline{BHE}$ LOW to Write End	50		50		55		ns
t_{SD}	Data Set-up to Write End	25		25		25		ns
t_{HD}	Data Hold from Write End	0		0		0		ns
t_{HZWE}	$\overline{WE}$ LOW to High Z[11, 12]		25		25		25	ns
t_{LZWE}	$\overline{WE}$ HIGH to Low Z[11, 12]	5		5		5		ns

Switching Waveforms

Read Cycle 1 (Address Transition Controlled)[14, 15, 16]



Read Cycle 2 ($\overline{OE}$ Controlled)[14, 16]



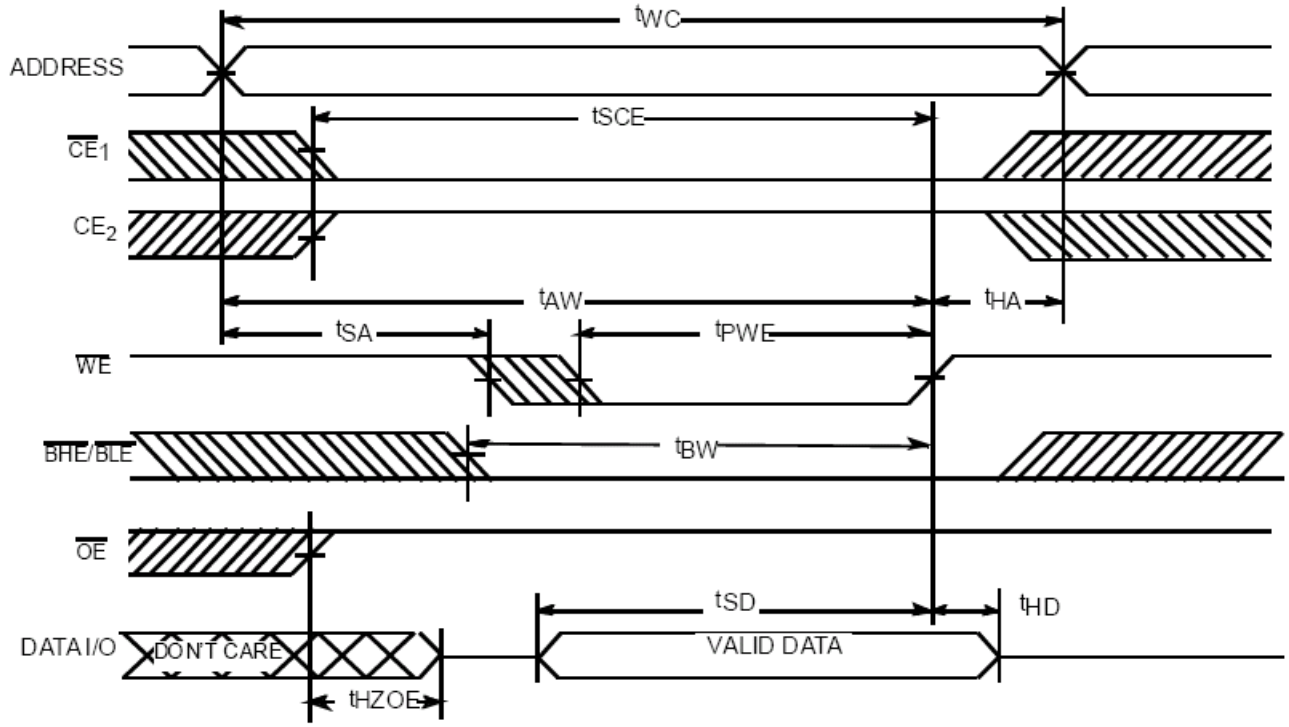
Notes:

15.Device is continuously selected. $\overline{OE}$, $\overline{CE}$ = V_{IL}.

16. $\overline{WE}$ is HIGH for Read Cycle.

Switching Waveforms (continued)

Write Cycle No. 1($\overline{WE}$ Controlled)[12, 13, 17, 18, 19]



Notes:

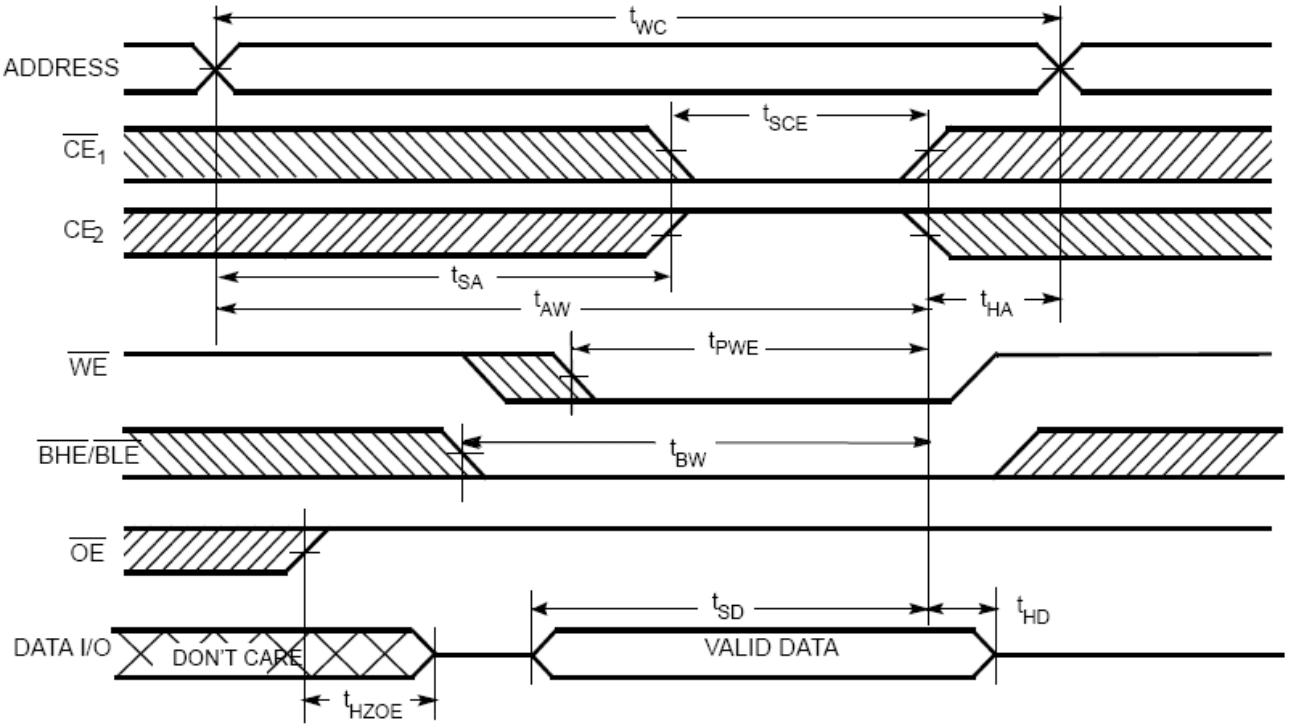
17.Data I/O is high impedance if $\overline{OE}$ > V_{IH}.

18.If Chip Enable goes INACTIVE simultaneously with $\overline{WE}$ =HIGH, the output remains in a high-impedance state.

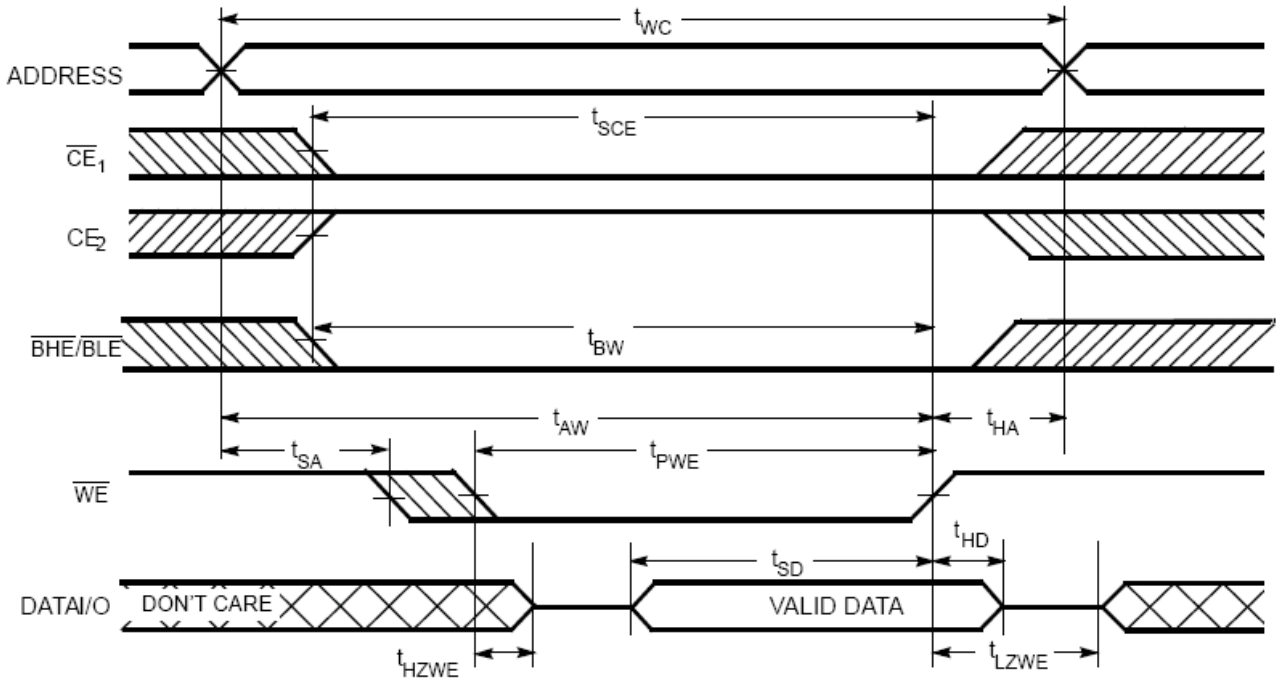
19.During the DON'T CARE period in the DATA I/O waveform, the I/Os are in output state and input signals should not be applied.

Switching Waveforms (continued)

Write Cycle 2 ($\overline{CE}_1$ or CE2 Controlled)[12, 13, 17, 18, 19]

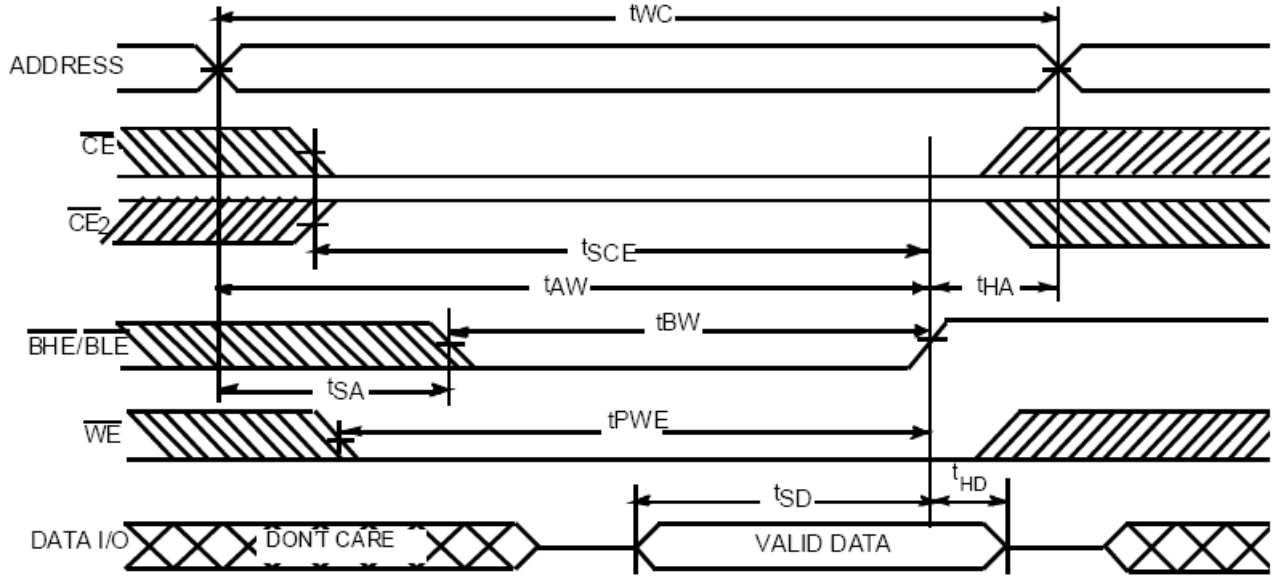


Write Cycle 3 ($\overline{WE}$ Controlled, $\overline{OE}$ LOW)[18, 19]



Switching Waveforms (continued)

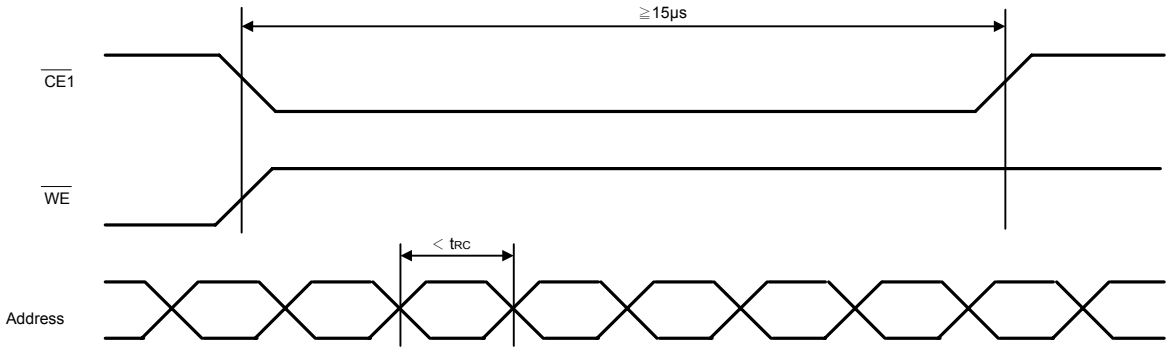
Write Cycle No. 4 ($\overline{BHE}$/$\overline{BLE}$ Controlled, $\overline{OE}$ LOW)[18, 19]



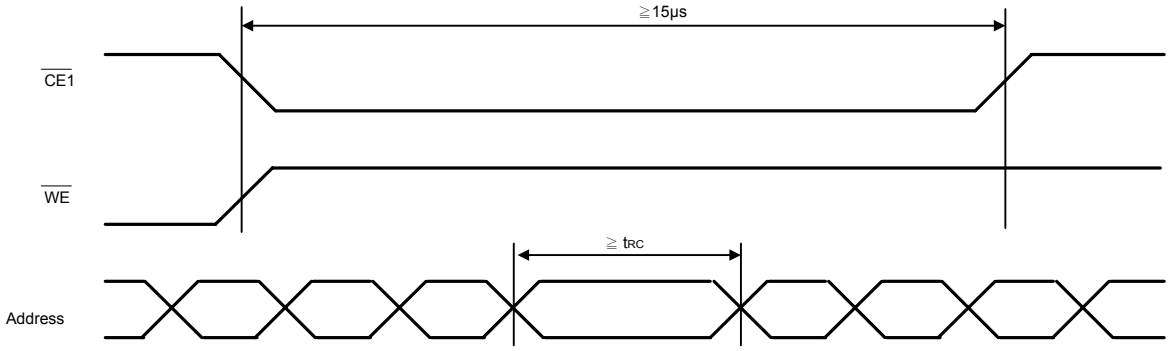
Avoid Timing

ESMT Pseudo SRAM has a timing which is not supported at read operation, If your system has multiple invalid address signal shorter than tRC during over 15μs at read operation shown as in Abnormal Timing, it requires a normal read timing at leat during 15μs shown as in Avoidable timing 1 or toggle $\overline{CE1}$ to high ($\geqq t_{RC}$) one time at least shown as in Avoidable Timing 2.

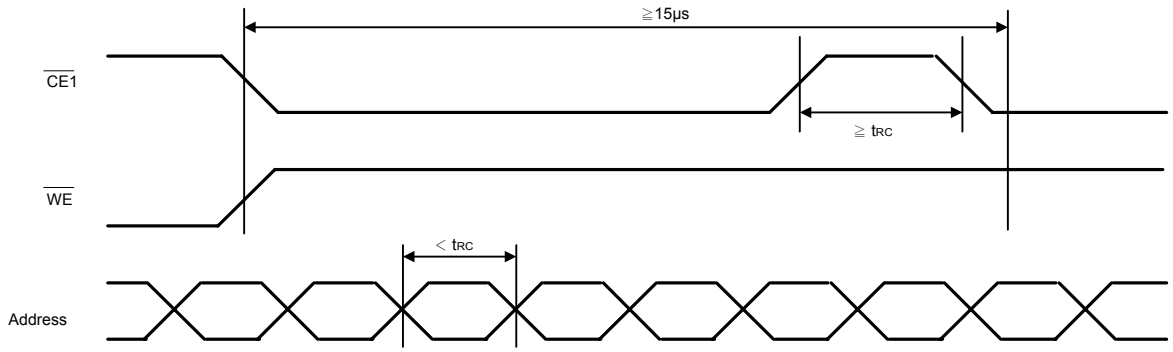
Abnormal Timing



Avoidable Timing 1



Avoidable Timing 2



Truth Table[20]

$\overline{CE}1$	CE2	$\overline{WE}$	$\overline{OE}$	$\overline{BHE}$	$\overline{BLE}$	Inputs/Outputs	Mode	Power
H	X	X	X	X	X	High Z	Deselect/Power-down	Standby (I_{SB})
X	L	X	X	X	X	High Z	Deselect/Power-down	Standby (I_{SB})
X	X	X	X	H	H	High Z	Deselect/Power-down	Standby (I_{SB})
L	H	H	L	L	L	Data Out (I/O_0–I/O_{15})	Read (Upper Byte and Lower Byte)	Active (I_{CC})
L	H	H	L	H	L	Data Out (I/O_0–I/O_7); I/O_8–I/O_{15} in High Z	Read (Upper Byte only)	Active (I_{CC})
L	H	H	L	L	H	Data Out (I/O_8–I/O_{15}); I/O_0–I/O_7 in High Z	Read (Lower Byte only)	Active (I_{CC})
L	H	H	H	L	L	High Z	Output Disabled	Active (I_{CC})
L	H	H	H	H	L	High Z	Output Disabled	Active (I_{CC})
L	H	H	H	L	H	High Z	Output Disabled	Active (I_{CC})
L	H	L	X	L	L	Data In (I/O_0–I/O_{15})	Write (Upper Byte and Lower Byte)	Active (I_{CC})
L	H	L	X	H	L	Data In (I/O_0–I/O_7); I/O_8–I/O_{15} in High Z	Write (Lower Byte Only)	Active (I_{CC})
L	H	L	X	L	H	Data In (I/O_8–I/O_{15}); I/O_0–I/O_7 in High Z	Write (Upper Byte Only)	Active (I_{CC})

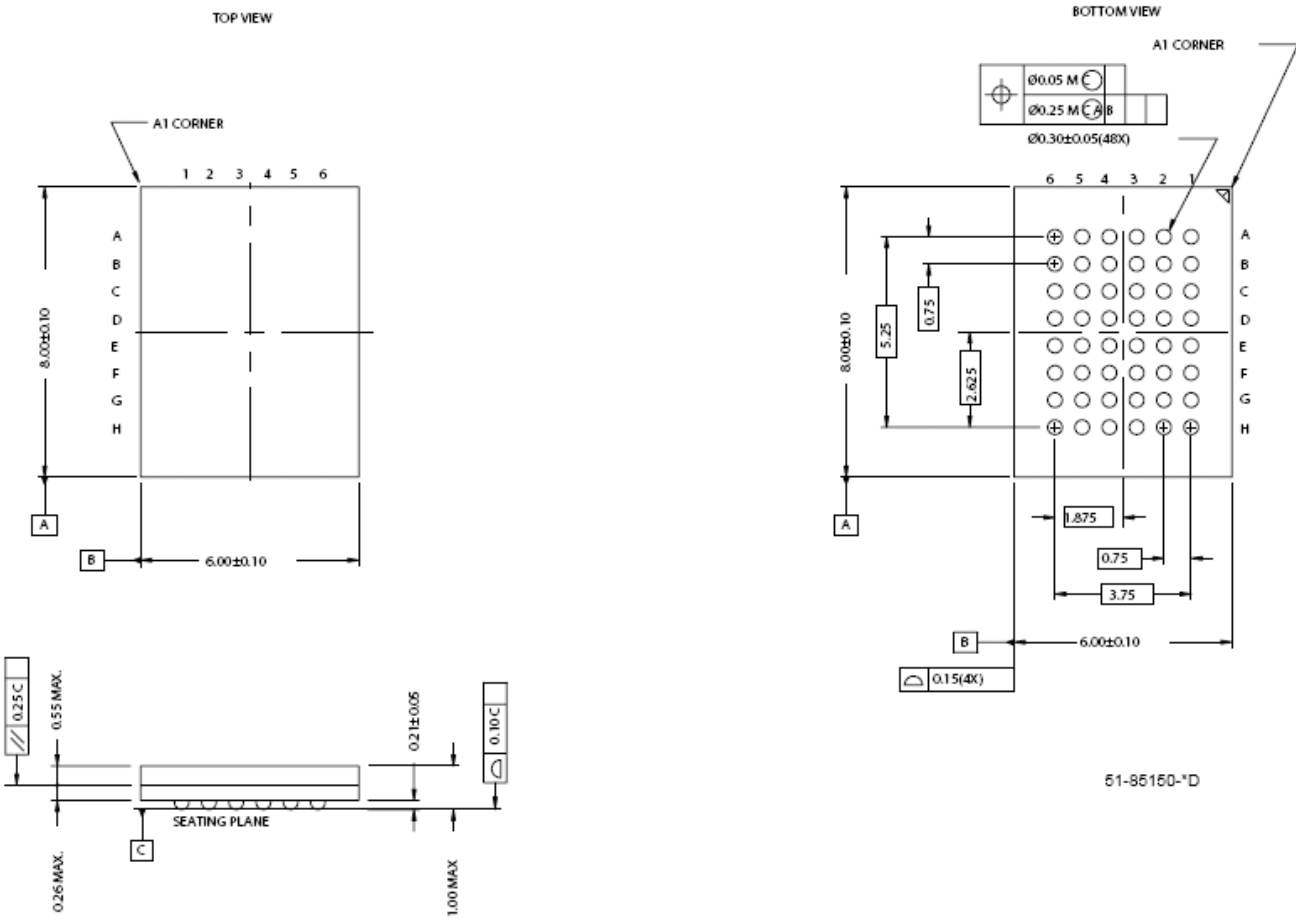
Note:
20.H = Logic HIGH, L = Logic LOW, X = Don't Care.

Ordering Information

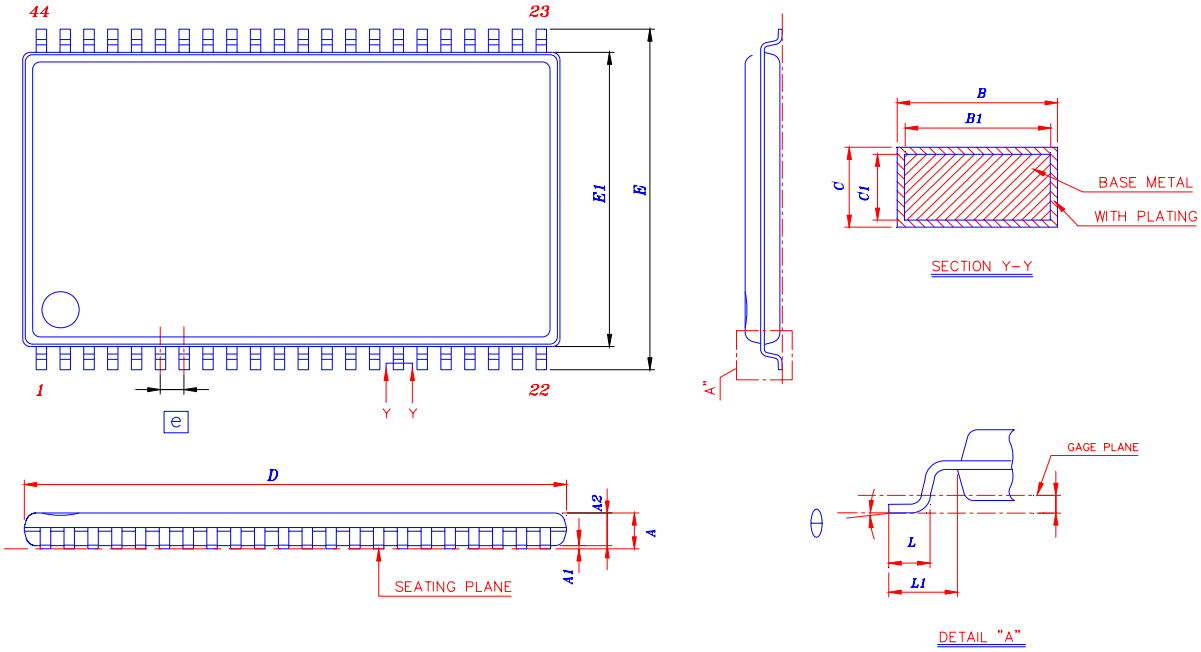
Speed (ns)	Ordering Code	Package Type	Operating Range
55	M24L416256DA-55BEG	48-ball Very Fine Pitch BGA (6.0 x 8.0 x 1.0 mm) (Pb-Free)	Extended
60	M24L416256DA-60BEG	48-ball Very Fine Pitch BGA (6.0 x 8.0 x 1.0 mm) (Pb-Free)	Extended
70	M24L416256DA-70BEG	48-ball Very Fine Pitch BGA (6.0 x 8.0 x 1.0 mm) (Pb-Free)	Extended
55	M24L416256DA-55TEG	44-pin TSOPII (Pb-Free)	Extended
60	M24L416256DA-60TEG	44-pin TSOPII (Pb-Free)	Extended
70	M24L416256DA-70TEG	44-pin TSOPII (Pb-Free)	Extended
55	M24L416256DA-55BIG	48-ball Very Fine Pitch BGA (6.0 x 8.0 x 1.0 mm) (Pb-Free)	Industrial
60	M24L416256DA-60BIG	48-ball Very Fine Pitch BGA (6.0 x 8.0 x 1.0 mm) (Pb-Free)	Industrial
70	M24L416256DA-70BIG	48-ball Very Fine Pitch BGA (6.0 x 8.0 x 1.0 mm) (Pb-Free)	Industrial
55	M24L416256DA-55TIG	44-pin TSOPII (Pb-Free)	Industrial
60	M24L416256DA-60TIG	44-pin TSOPII (Pb-Free)	Industrial
70	M24L416256DA-70TIG	44-pin TSOPII (Pb-Free)	Industrial

Package Diagram

48-ball VFBGA (6 x 8 x 1 mm)



44-LEAD TSOP(II) PSRAM(400mil)



Symbol	Dimension in mm			Dimension in inch		
	Min	Norm	Max	Min	Norm	Max
A	——	——	1.20	——	——	0.047
A1	0.05	——	0.15	0.002	——	0.006
A2	0.95	1.00	1.05	0.037	0.039	0.042
B	0.30	——	0.45	0.012	——	0.018
B1	0.30	0.35	0.40	0.012	0.014	0.016
C	0.12	——	0.21	0.005	——	0.008
C1	0.10	——	0.16	0.004	——	0.006
D	18.28	18.41	18.54	0.720	0.725	0.730
ZD	0.805 REF			0.0317 REF		
E	11.56	11.76	11.96	0.455	0.463	0.471
E1	10.03	10.16	10.29	0.395	0.400	0.4
L	0.40	0.59	0.69	0.016	0.023	0.027
L1	0.80 REF			0.031 REF		
e	0.80 BSC			0.0315 BSC		
θ	0°	——	8°	0°	——	8°

Revision History

Revision	Date	Description
1.0	2007.07.04	Original
1.1	2007.11.20	Modify the descriptive error for standby mode, t_{HZWE} and t_{LZWE} description
1.2	2007.11.22	Modify t_{HZBE} and t_{LZBE} descriptive and restore t_{HZWE} and t_{LZWE} description
1.3	2008.02.27	1.Add 44-pin TSOPII package 2. Add Avoid timing
1.4	2008.03.24	Add I-grade for TSOPII package
1.5	2008.07.04	1. Move Revision History to the last 2. Modify voltage range 2.7V~3.3V to 2.7V~3.6V 3. Add Industrial grade for BGA package

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